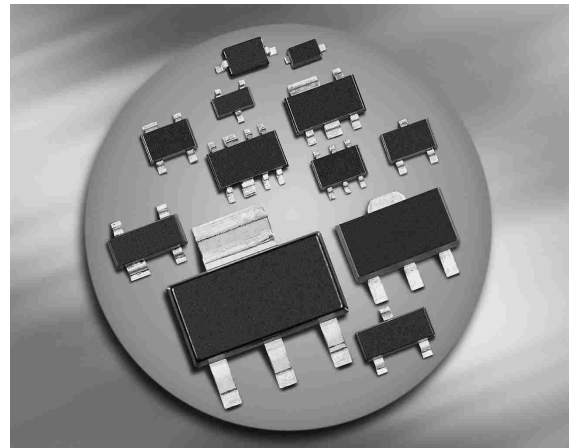


PNP Silicon AF Transistor

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 Hz and 15 kHz
- Complementary types:
BC846...-BC850... (NPN)
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



¹Pb-containing package may be available upon special request

Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BC856A	3As	1=B	2=E	3=C	-	-	-	SOT23
BC856B	3Bs	1=B	2=E	3=C	-	-	-	SOT23
BC856BW	3Bs	1=B	2=E	3=C	-	-	-	SOT323
BC857A	3Es	1=B	2=E	3=C	-	-	-	SOT23
BC857B	3Fs	1=B	2=E	3=C	-	-	-	SOT23
BC857BF*	3Fs	1=B	2=E	3=C	-	-	-	TSFP-3
BC857BL3	3F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC857BW	3Fs	1=B	2=E	3=C	-	-	-	SOT323
BC857C	3Gs	1=B	2=E	3=C	-	-	-	SOT23
BC857CW	3Gs	1=B	2=E	3=C	-	-	-	SOT323
BC858A	3Js	1=B	2=E	3=C	-	-	-	SOT23
BC858B	3Ks	1=B	2=E	3=C	-	-	-	SOT23
BC858BL3	3K	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC858BW	3Ks	1=B	2=E	3=C	-	-	-	SOT323
BC858C	3Ls	1=B	2=E	3=C	-	-	-	SOT23
BC858CW	3Ls	1=B	2=E	3=C	-	-	-	SOT323
BC859C	4Cs	1=B	2=E	3=C	-	-	-	SOT23
BC860B	4Fs	1=B	2=E	3=C	-	-	-	SOT23
BC860BW	4Fs	1=B	2=E	3=C	-	-	-	SOT323
BC860CW	4Gs	1=B	2=E	3=C	-	-	-	SOT323

* Not for new design

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BC856...		65	
BC857..., BC860...		45	
BC858..., BC859...		30	
Collector-base voltage	V_{CBO}		
BC856...		80	
BC857..., BC860...		50	
BC858..., BC859...		30	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation	P_{tot}		mW
$T_S \leq 71$ °C, BC856-BC860		330	
$T_S \leq 128$ °C, BC857BF-BC858BF		250	
$T_S \leq 135$ °C, BC857BL3, BC860BL3		250	
$T_S \leq 124$ °C, BC856W-BC860W		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BC856-BC860		≤ 240	
BC857BF-BC858BF		≤ 90	
BC857BL3, BC858BL3		≤ 60	
BC856W-BC860W		≤ 105	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BC856... $I_C = 10\text{ mA}$, $I_B = 0$, BC857..., BC860... $I_C = 10\text{ mA}$, $I_B = 0$, BC858..., BC859...	$V_{(BR)CEO}$	65 45 30	- - -	- - -	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC856... $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC857..., BC860... $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC858..., BC859...	$V_{(BR)CBO}$	80 50 30	- - -	- - -	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 45\text{ V}$, $I_E = 0$ $V_{CB} = 30\text{ V}$, $I_E = 0$, $T_A = 150^\circ\text{C}$	I_{CBO}	- -	- -	0.015 5	μA
DC current gain ¹⁾ $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.A $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.B $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.C $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.A $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.B $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$, h_{FE} -grp.C	h_{FE}	- - - 125 220 420	140 250 480 180 290 520	- - - 250 475 800	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	75 250	300 650	mV
Base emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 850	- -	
Base-emitter voltage ¹⁾ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820	

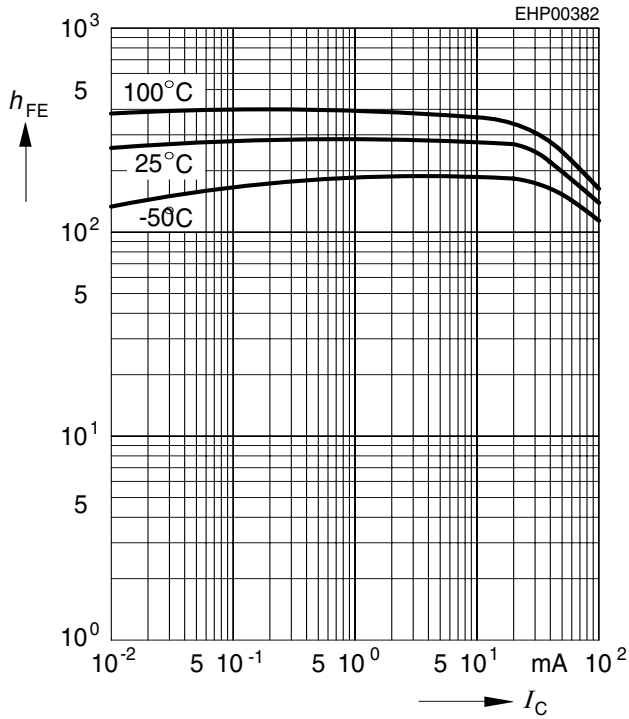
¹⁾Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 20\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.C}$	h_{11e}	-	2.7 4.5 8.7	-	k Ω
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.C}$	h_{12e}	-	1.5 2 3	-	10^{-4}
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.C}$	h_{21e}	-	200 330 600	-	-
Open-circuit output admittance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.A}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.B}$ $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}, h_{FE}\text{-grp.C}$	h_{22e}	-	18 30 60	-	μS
Noise figure $I_C = 0.2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz},$ D $f = 200\text{ Hz}, R_S = 2\text{ k}\Omega, \text{BC859, BC850}$	F	-	1	4	dB
Equivalent noise voltage $I_C = 200\text{ mA}, V_{CE} = 5\text{ V}, R_S = 2\text{ k}\Omega,$ $f = 10\text{...}50\text{ Hz}, \text{BC860}$	V_n	-	-	0.11	μV

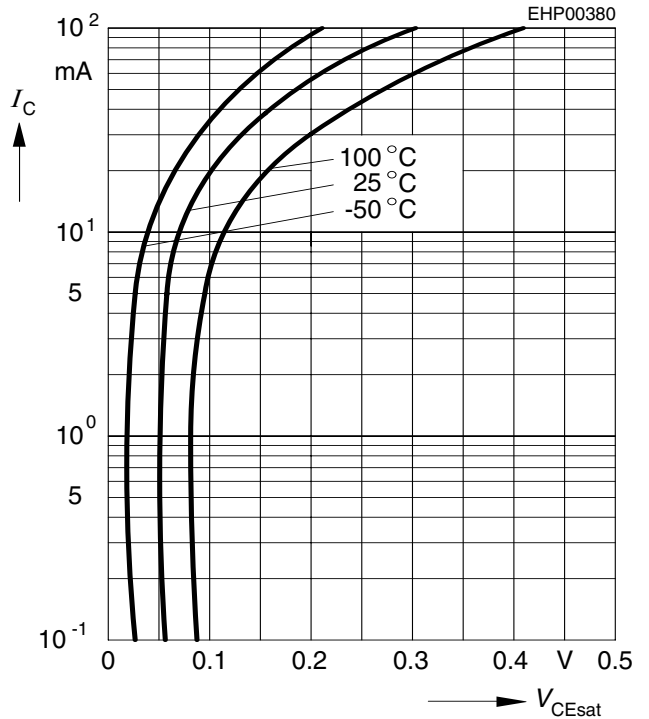
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 1\text{ V}$



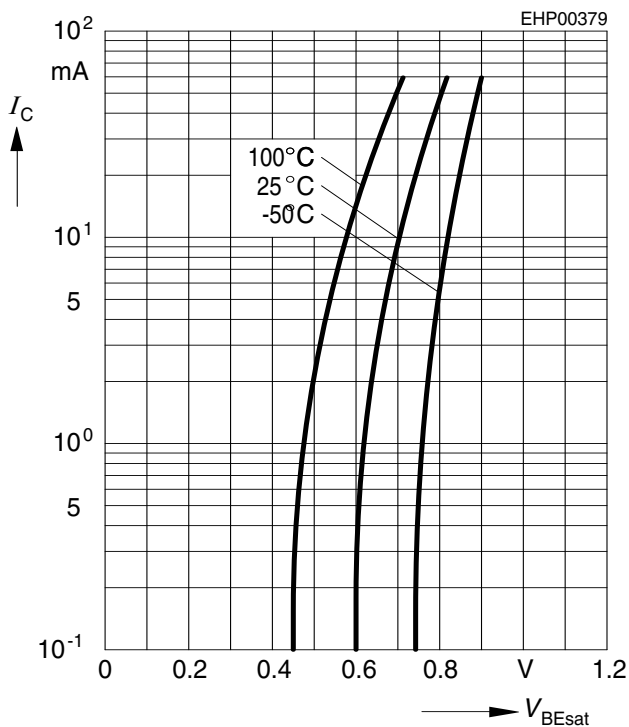
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 20$



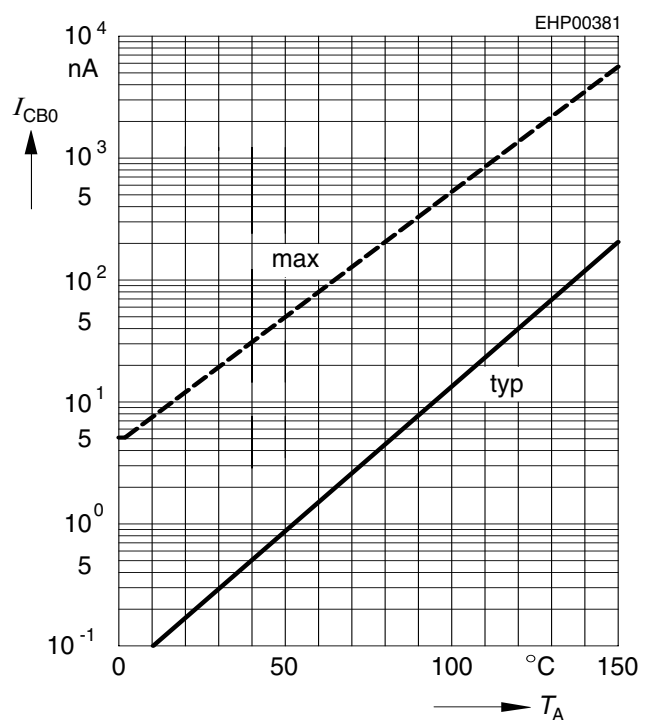
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 20$



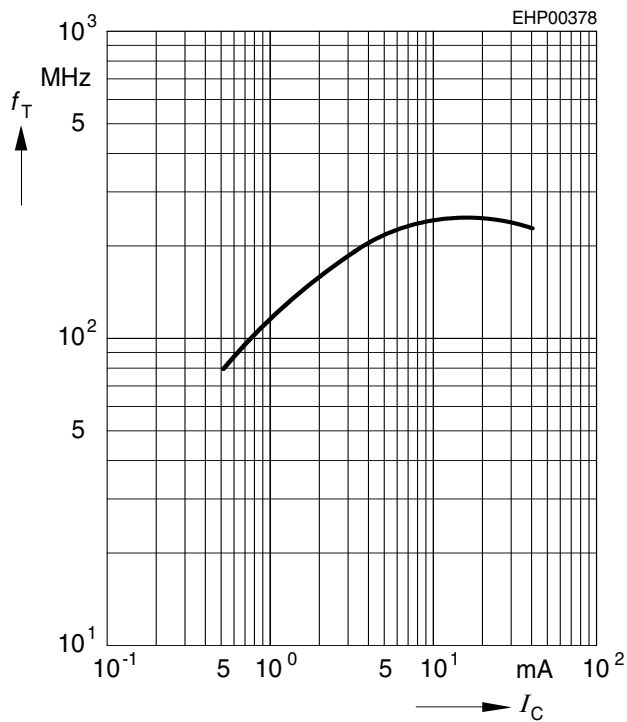
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30\text{ V}$



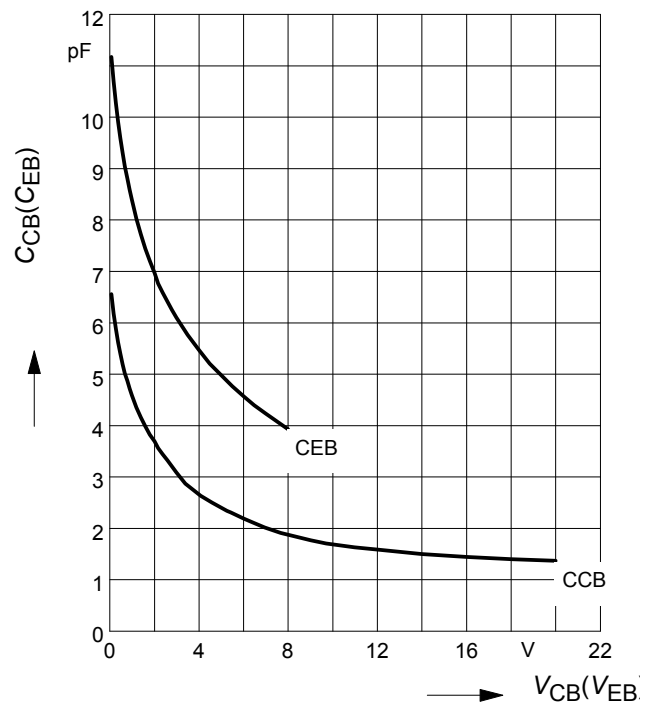
Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\text{ V}$



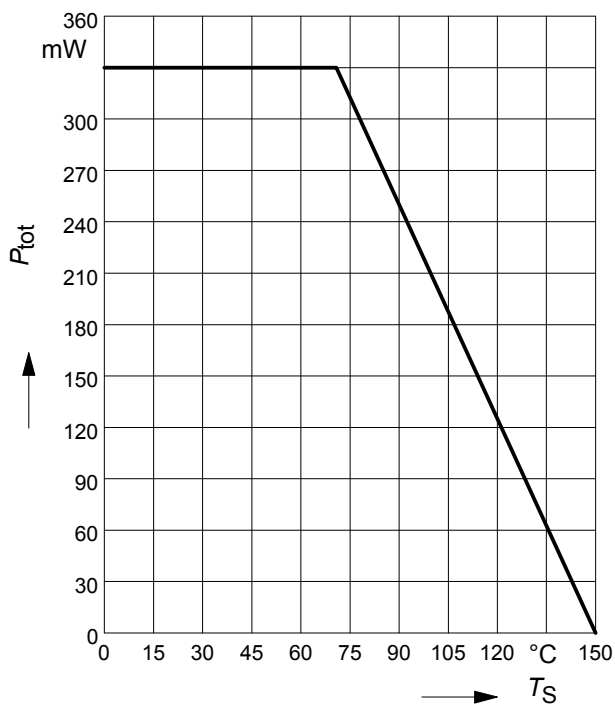
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



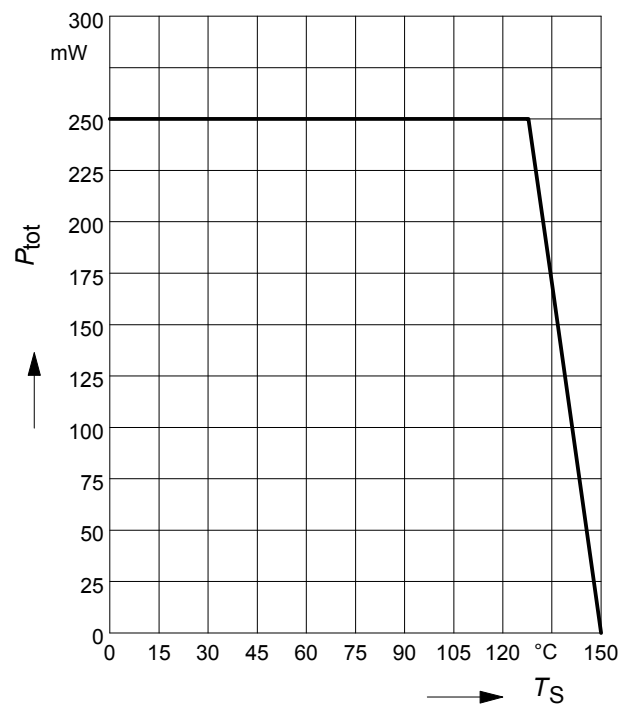
Total power dissipation $P_{tot} = f(T_S)$

BC856-BC860



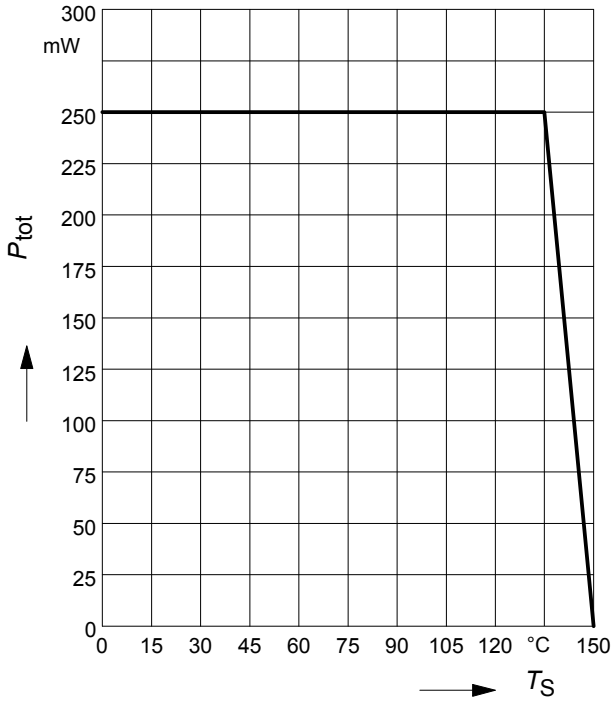
Total power dissipation $P_{tot} = f(T_S)$

BC857BF, BC858BF



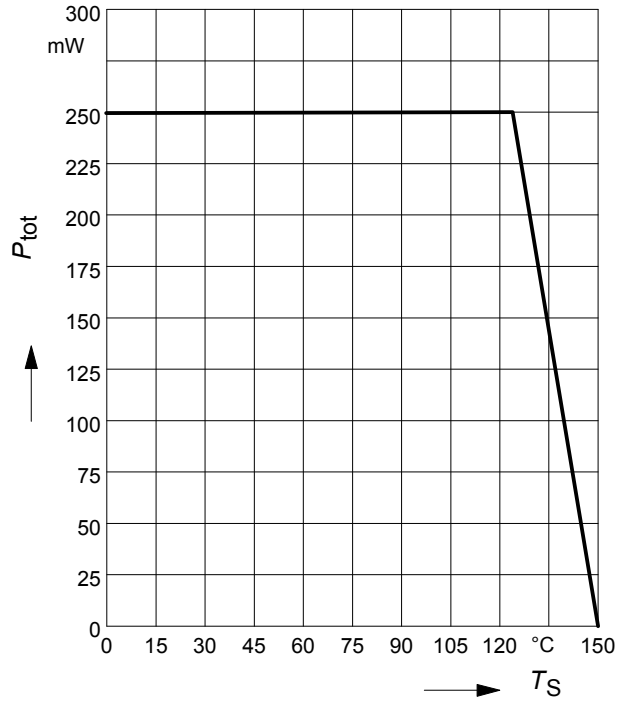
Total power dissipation $P_{tot} = f(T_S)$

BC857BL3, BC858BL3



Total power dissipation $P_{tot} = f(T_S)$

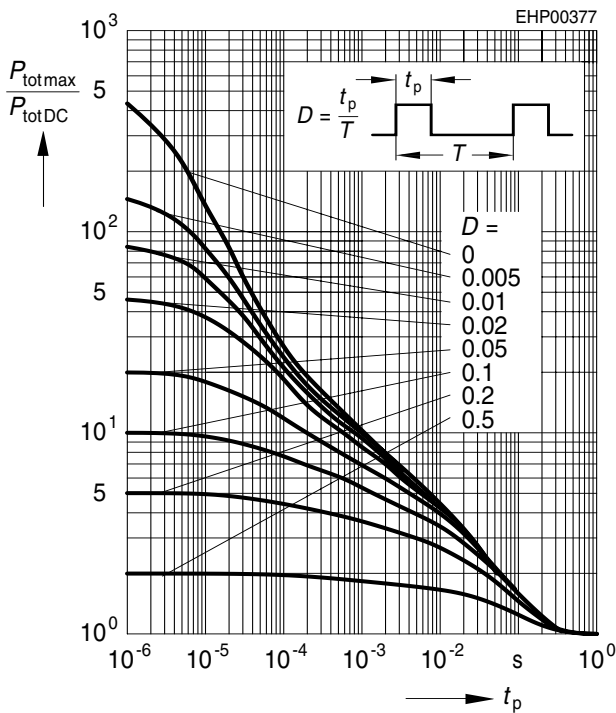
BC856W-BC860W



Permissible Pulse Load

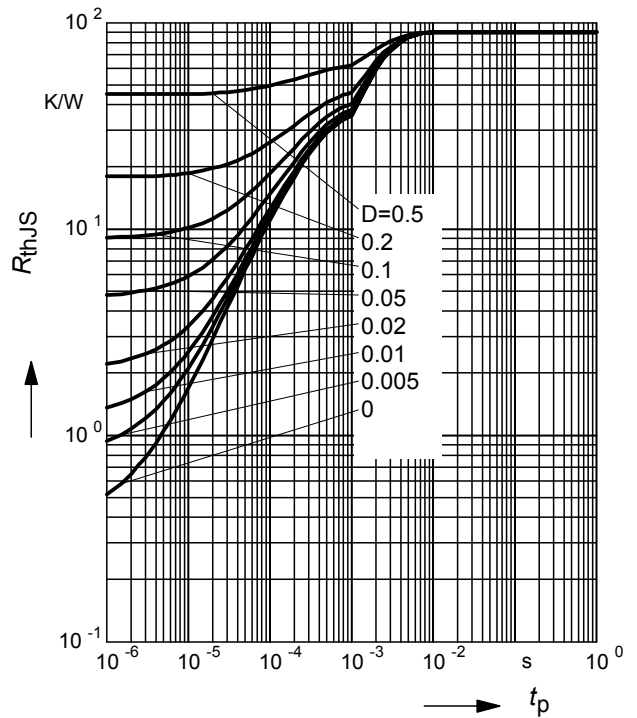
$P_{totmax}/P_{totDC} = f(t_p)$

BC856/W-BC860/W



Permissible Puls Load $R_{thJS} = f(t_p)$

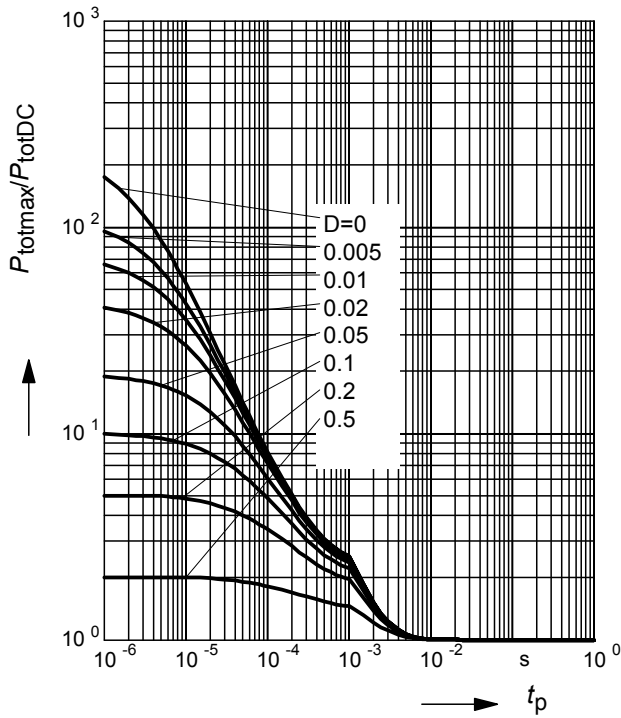
BC857BF, BC858BF



Permissible Pulse Load

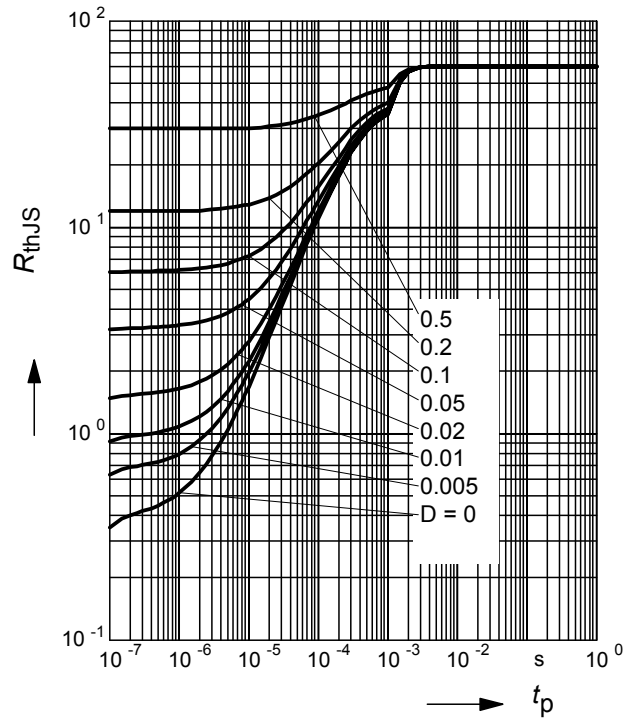
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BC857BF, BC858BF



Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

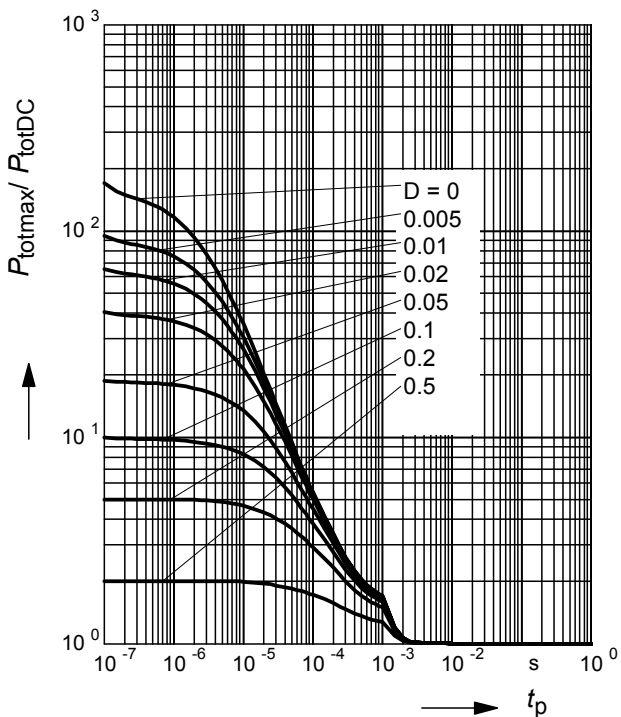
BC857BL3, BC858BL3



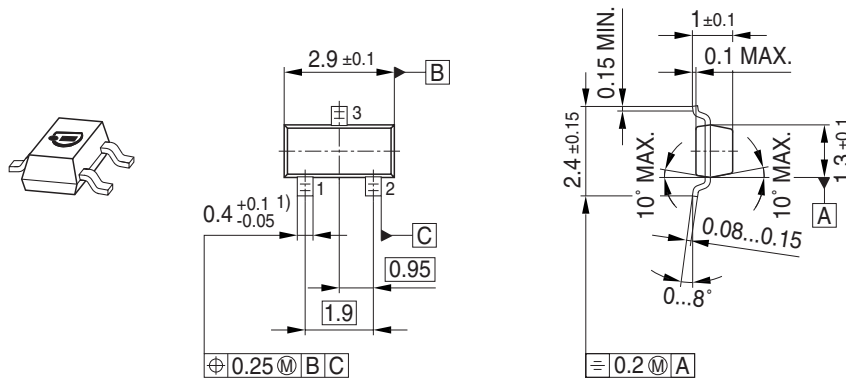
Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BC857BL3, BC858BL3

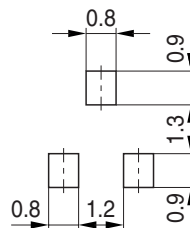


Package Outline

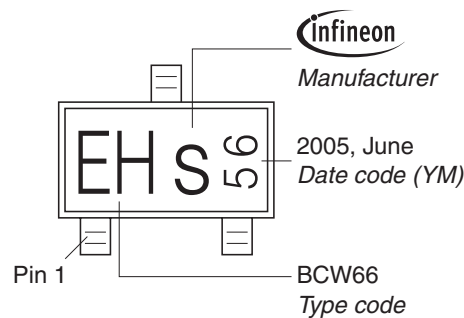


1) Lead width can be 0.6 max. in dambar area

Foot Print

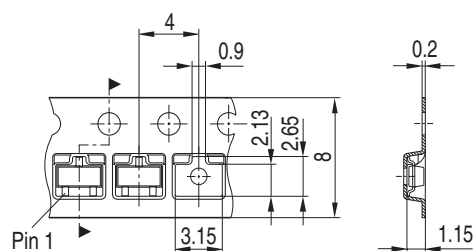


Marking Layout (Example)

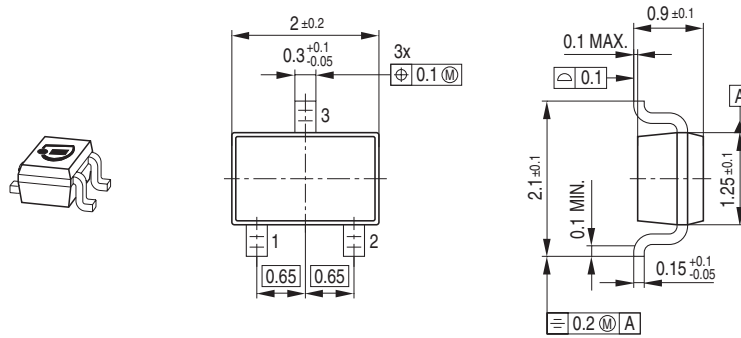


Standard Packing

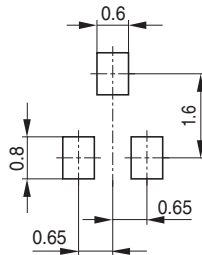
Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



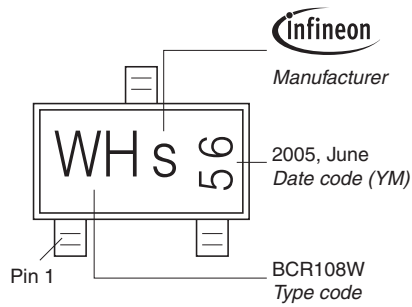
Package Outline



Foot Print

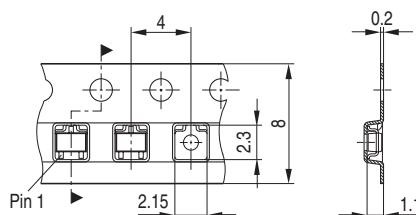


Marking Layout (Example)

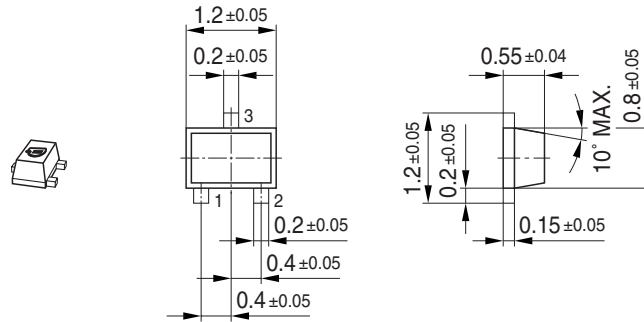


Standard Packing

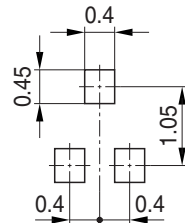
Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



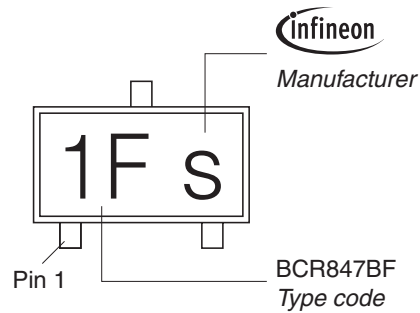
Package Outline



Foot Print

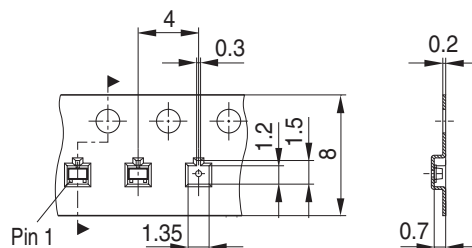


Marking Layout (Example)

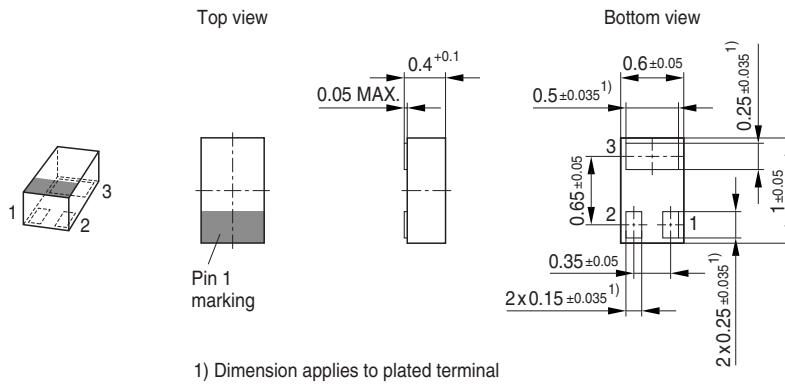


Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

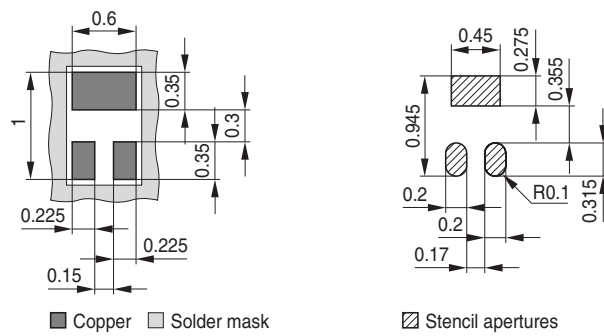


Package Outline

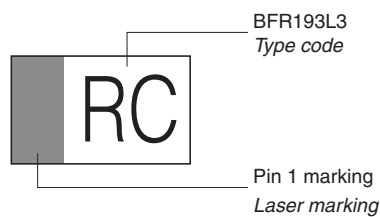


Foot Print

For board assembly information please refer to Infineon website "Packages"

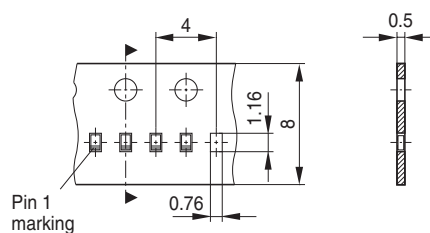


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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